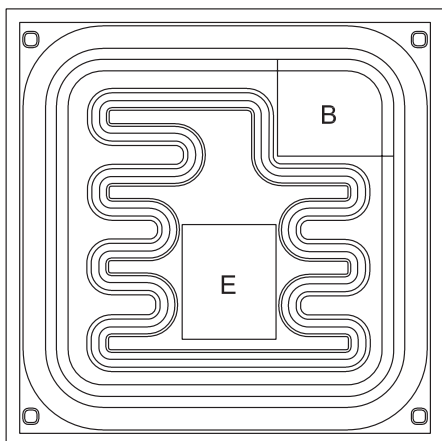


**PROCESS DETAILS**

Process	EPITAXIAL PLANAR
Die Size	16.5 x 16.5 MILS
Die Thickness	7.1 MILS
Base Bonding Pad Area	3.5 x 4.3 MILS
Emitter Bonding Pad Area	3.5 x 4.3 MILS
Top Side Metalization	Al - 30,000Å
Back Side Metalization	Au-As - 13,000Å

**GEOMETRY**



BACKSIDE COLLECTOR

R2

**GROSS DIE PER 4 INCH WAFER**

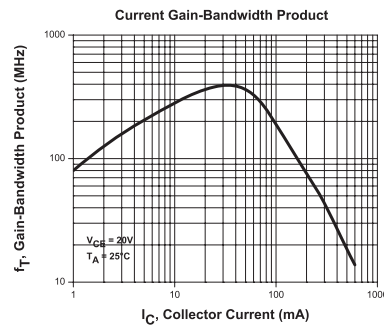
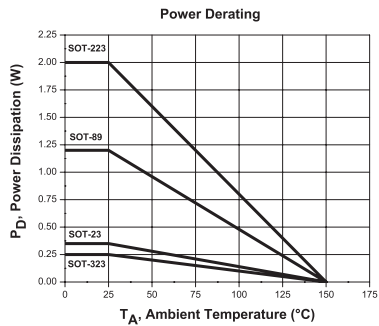
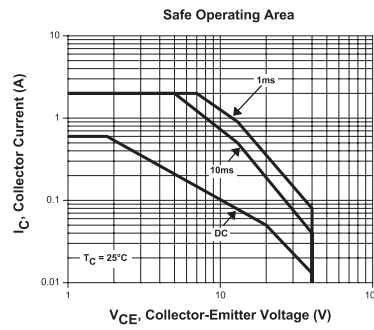
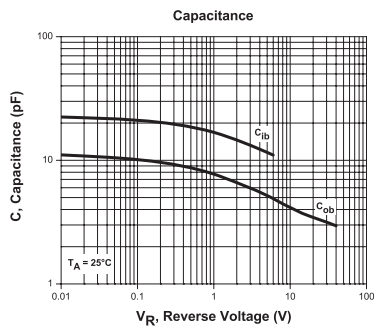
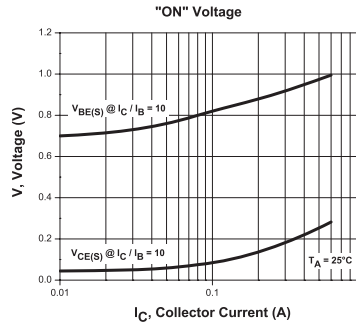
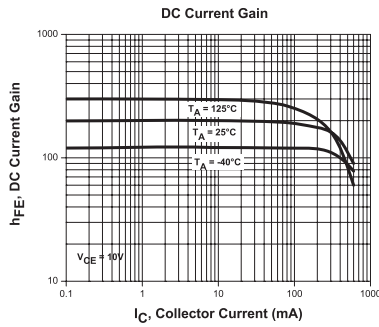
41,690

**PRINCIPAL DEVICE TYPES**

CMLT2222A  
CMLT2207  
CMLM2205  
CMKT2207

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